Application No. 10/816,502

Amendment filed: June 23, 2005

Reply to Office Action of April 19, 2005

IN THE CLAIMS

Current Listing Of Claims:

1. (Currently Amended) A photoacid generator, comprising:

an antenna group comprising diphenyliodonium; and

a carborane-based group.

2. (Original) The photoacid generator of claim 1, wherein the carborane-based group is

halogenated by between one and six halogens.

3. (Original) The photoacid generator of claim 2, wherein the carborane-based group is

hexachlorocarborane.

4. (Original) The photoacid generator of claim 1, wherein the carborane-based group is

functionalized on at least one boron atom by a group having a high electronegativity.

5. (Original) The photoacid generator of claim 1, wherein the carborane-based group is

functionalized by an etch-resistant group.

6. (Original) The photoacid generator of claim 1, wherein the carborane-based group is

functionalized on a boron atom by an alkyl group.

7. (Original) The photoacid generator of claim 1, wherein the carborane-based group is

functionalized on a carbon atom by a group that modifies the polarity of the cationic

carborane.

-2-

Application No. 10/816,502 Amendment filed: June 23, 2005 Reply to Office Action of April 19, 2005

8. (Cancelled)
9. (Original) A composition, comprising:
a photoacid generator moiety comprising a carborane;
a photoimageable species; and
a quencher.
10. (Original) The composition of claim 9, wherein the composition is formulated to serve as a 193nm photoresist.
11. (Original) The composition of claim 9, wherein the composition is formulated to serve as an EUV photoresist.
12. (Original) The composition of claim 9, wherein the EUV photoresist is sensitive to light
having a wavelength of 13.5nm.
13. (Currently Amended) A composition, comprising: — a photoacid generator moiety comprising a carborane; — a photoimageable species; — a quencher; and — the reaction products thereof. The composition of claim 0, forther comprising reaction products of the composition
The composition of claim 9, further comprising reaction products of the composition.

14. (Currently Amended) The composition of claim 13 9, further comprising an additive.

Application No. 10/816,502

Amendment filed: June 23, 2005

Reply to Office Action of April 19, 2005

15. (Currently Amended) The composition of claim 13 9, wherein the additive is in the

approximate range of 0.1 - 5% by weight of the composition.

16. (Currently Amended) The composition of claim 13 9, further comprising a solvent.

17. (Original) The composition of claim 16, wherein the solvent is in the approximate range

of 1% - 5% by weight of the composition.

18. (Currently Amended) The composition of claim 13 9, wherein the photoacid generator

moiety comprising a carborane is in the approximate range of 0.1% and 5% by weight of the

composition.

19. (Currently Amended) The composition of claim 13 9, wherein the photoacid generator

moiety comprising a carborane is in the approximate range of 0.5% and 2.5% by weight of

the composition.

20. (Previously Presented) The composition of claim 13 9, wherein the photoimageable

species is a polymer.

21. (Previously Presented) The composition of claim 13 9, wherein the photoimageable

species is in the approximate range of 80% and 97% by weight of the composition.

22. - 24. (Cancelled)

-4-

Application No. 10/816,502

Amendment filed: June 23, 2005

Reply to Office Action of April 19, 2005

25. (Original) A method comprising:

applying a photoresist to a substrate, the photoresist comprising a carborane-based

photoacid generator;

patterning the photoresist by irradiating the photoresist; and

etching the substrate.

26. (Original) The method of claim 25, wherein applying a photoresist to the substrate

comprises applying a chemically amplified photoresist to the substrate.

27. (Original) The method of claim 26, wherein the chemically amplified resist is a high

activation energy resist.

28. (Original) The method of claim 25, wherein patterning the photoresist by irradiating the

photoresist comprises exposing the photoresist to light having a wavelength of 193nm.

29. (Original) The method of claim 25, wherein patterning the photoresist by irradiating the

photoresist comprises exposing the photoresist to light having a wavelength in the extreme

ultraviolet region of the spectrum.

30. (Original) The method of claim 29, wherein the wavelength in the extreme ultraviolet

region of the spectrum is 13.5nm.

-5-